

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
100V	22mΩ @ V _{GS} = 10V	51.7A
	30mΩ @ V _{GS} = 6V	44.3A
	43.7mΩ @ V _{GS} = 4.5V	36.7A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

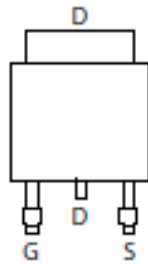
- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_G – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMTH10H025LK3Q](#))**

Mechanical Data

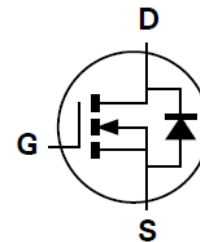
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓜ3
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



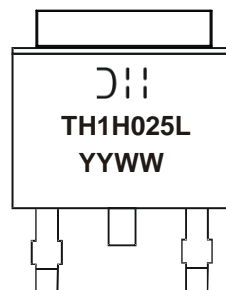
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H025LK3-13	TO252 (DPAK)	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



= Manufacturer's Marking
 TH1H025L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 18 = 2018)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 6)	I _D	T _C = +25°C	51.7
		T _C = +100°C	36.6
Pulsed Drain Current (10µs Pulse, T _C = +25°C, Package Limited)	I _{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	77	A
Pulsed Body Diode Forward Current (10µs Pulse, T _C = +25°C, Package Limited)	I _{SM}	200	A
Avalanche Current, L = 0.1mH	I _{AS}	15.8	A
Avalanche Energy, L = 0.1mH	E _{AS}	12.5	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	48	°C/W
Total Power Dissipation (Note 6)	P _D	Steady State	100
			100
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 80V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17.1	22	mΩ	V _{GS} = 10V, I _D = 20A
		—	21.4	30		V _{GS} = 6V, I _D = 20A
		—	28.3	43.7		V _{GS} = 4.5V, I _D = 20A
		—	—	—		V _{GS} = 0V, I _S = 20A
Diode Forward Voltage	V _{SD}	—	—	1.3	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1477	—	pF	V _{DS} = 50V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	263	—		
Reverse Transfer Capacitance	C _{RSS}	—	20	—		
Gate Resistance	R _G	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _G	—	21	—	nC	V _{DD} = 50V, I _D = 20A, V _{GS} = 10V
Gate-Source Charge	Q _{GS}	—	5.7	—		
Gate-Drain Charge	Q _{GD}	—	3.8	—		
Turn-On Delay Time	t _{D(ON)}	—	6.3	—	ns	V _{DD} = 50V, V _{GS} = 10V, I _D = 20A, R _G = 6Ω
Turn-On Rise Time	t _R	—	9.4	—		
Turn-Off Delay Time	t _{D(OFF)}	—	16.7	—		
Turn-Off Fall Time	t _F	—	8.2	—		
Reverse Recovery Time	t _{RR}	—	38.7	—	ns	I _F = 20A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	53.7	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

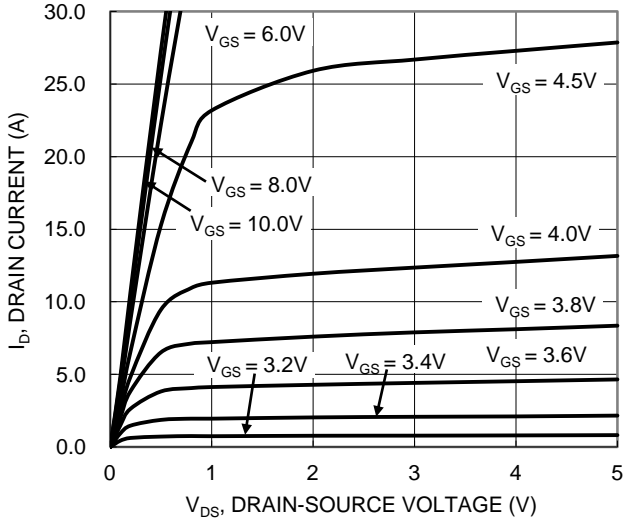


Figure 1. Typical Output Characteristic

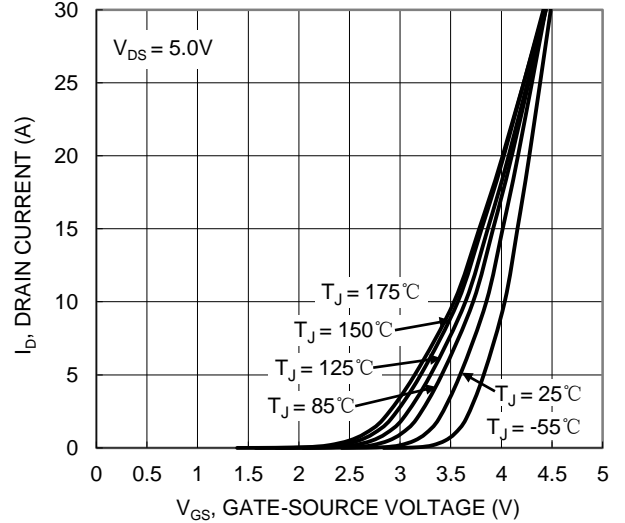


Figure 2. Typical Transfer Characteristic

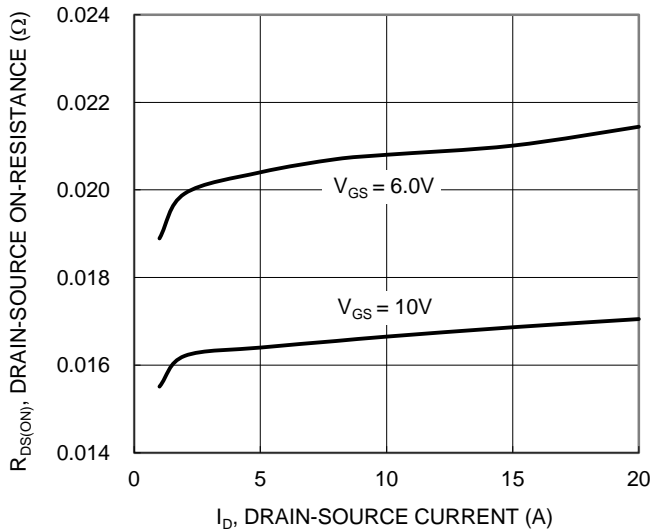


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

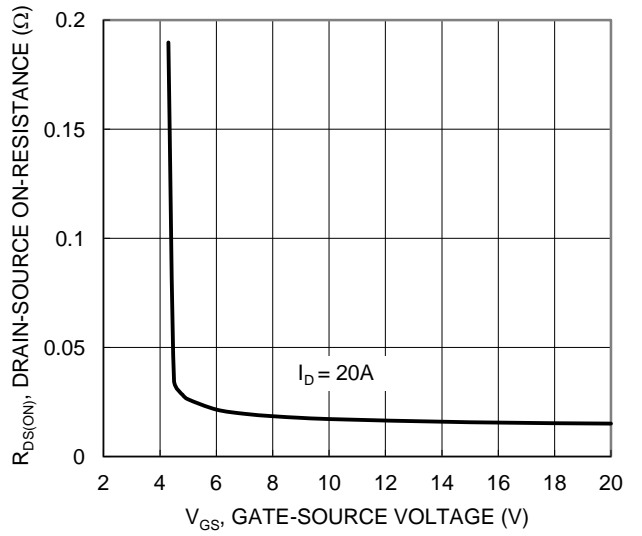


Figure 4. Typical Transfer Characteristic

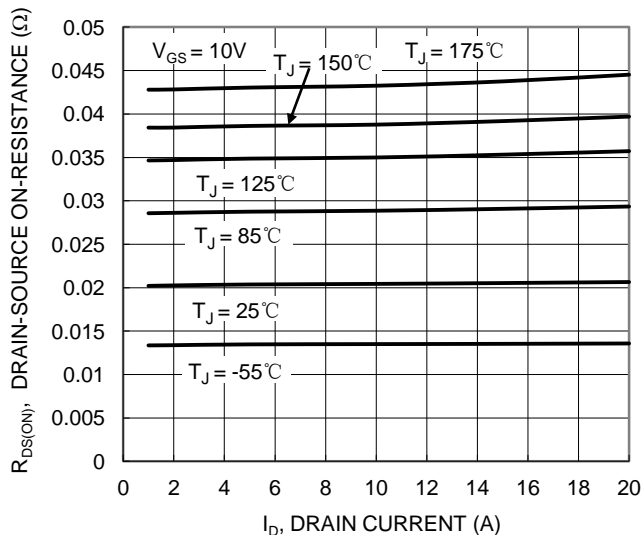


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

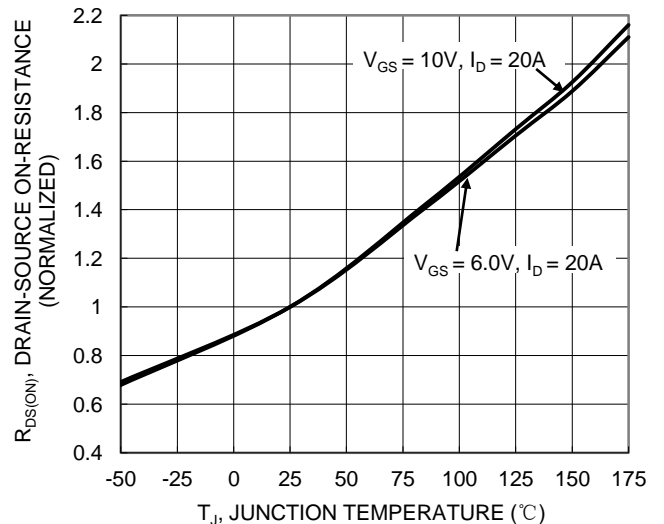
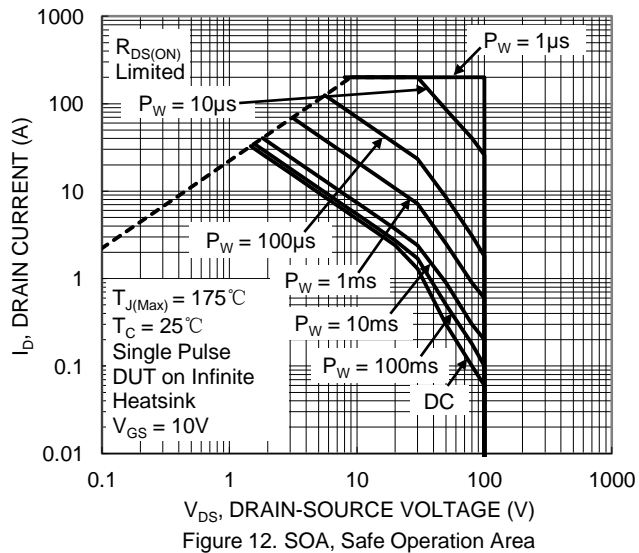
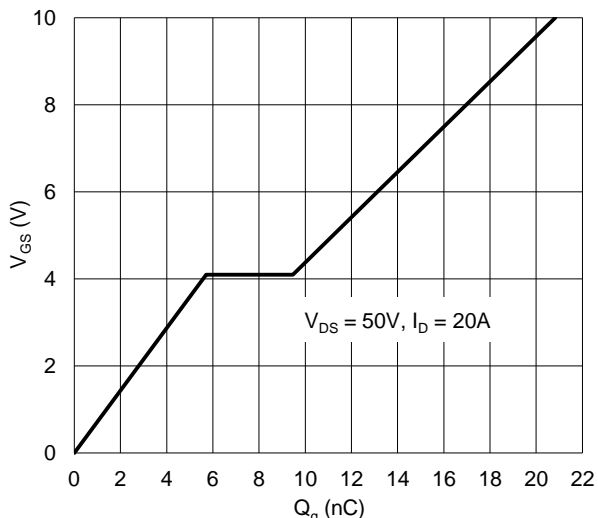
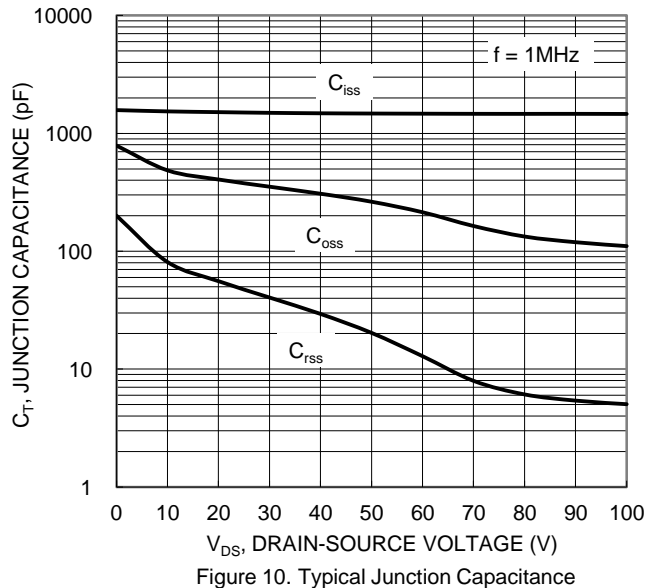
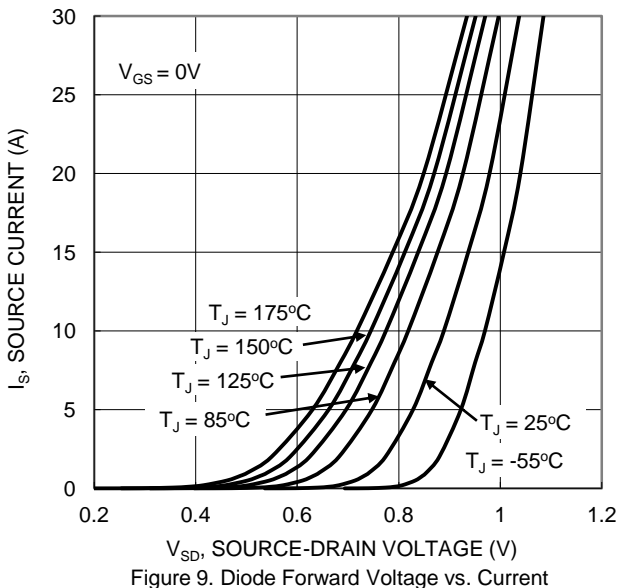
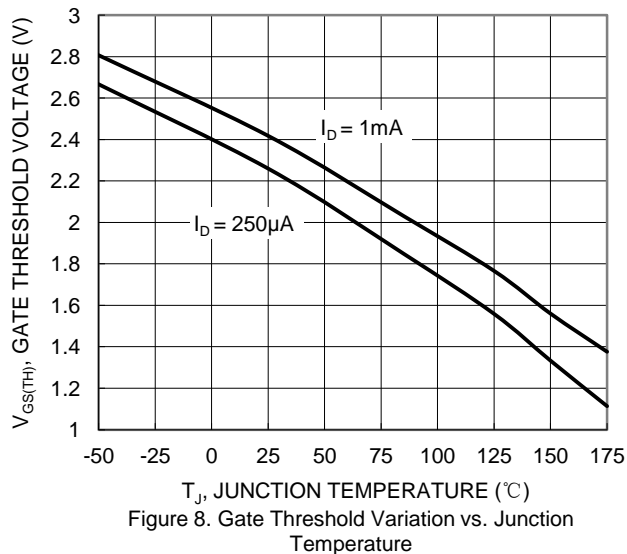
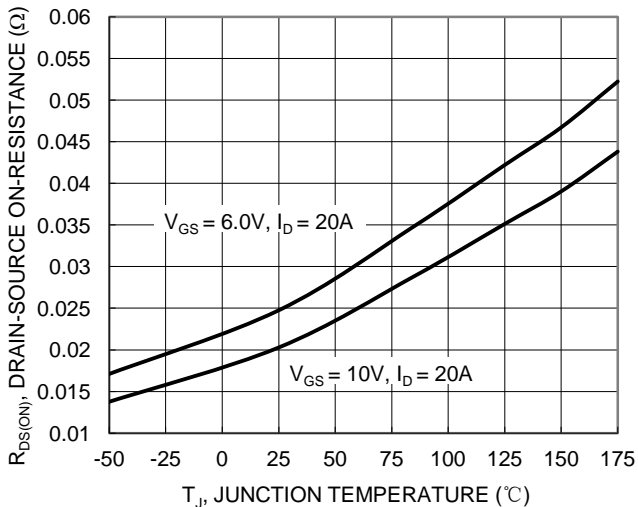


Figure 6. On-Resistance Variation with Temperature



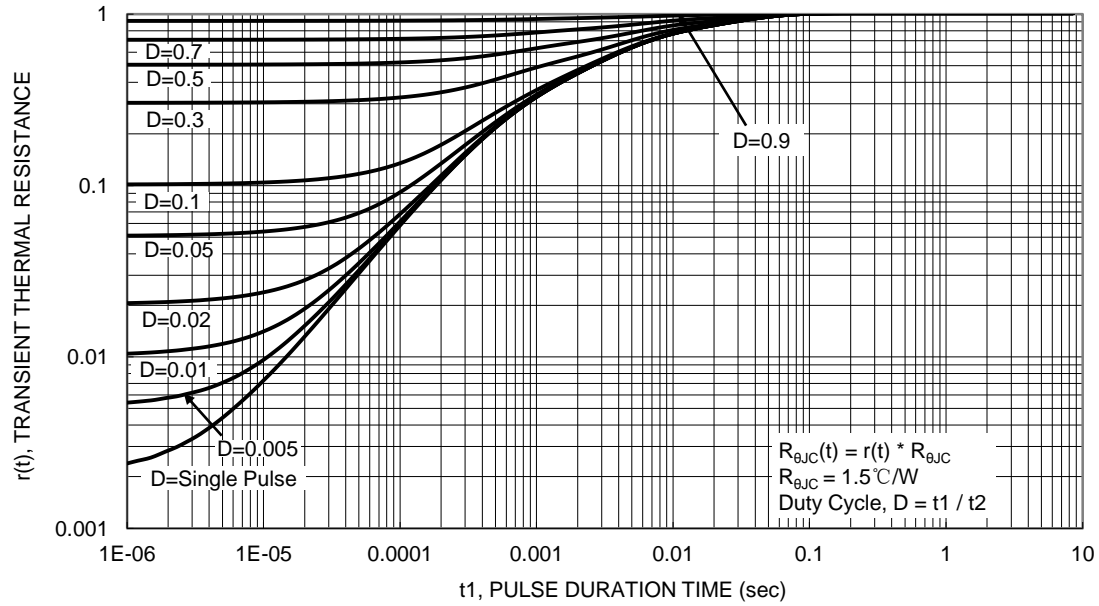
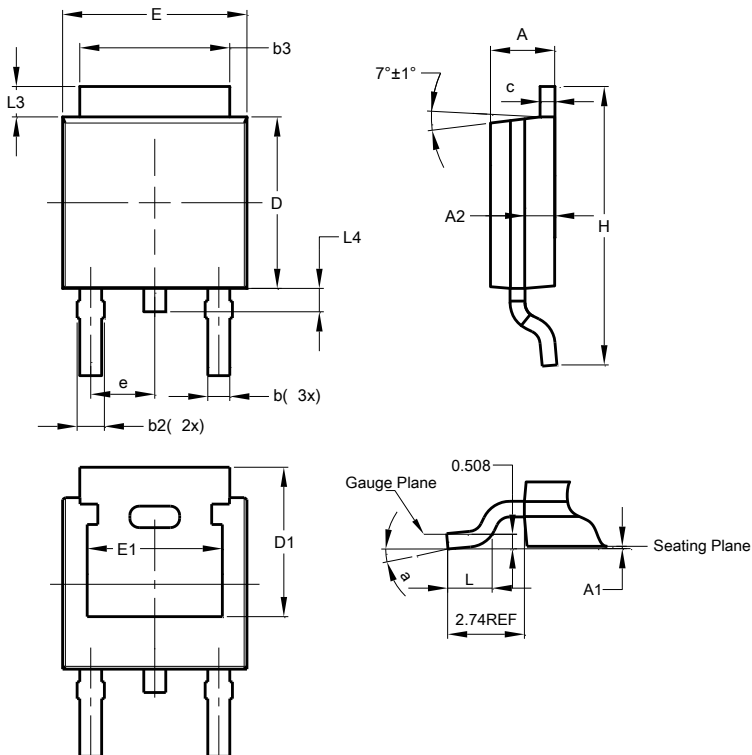


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

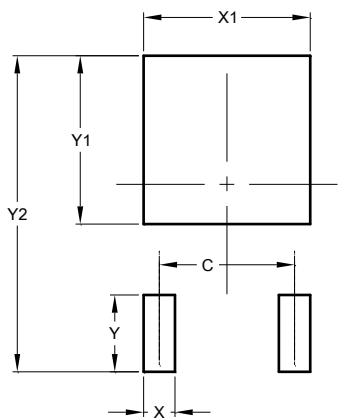


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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